

QORVO

SiC JFET Division

Is Now Part of

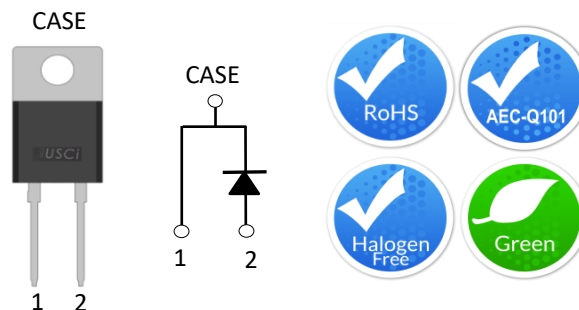
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Description

United Silicon Carbide, Inc. offers the 3rd generation of high performance SiC Merged-PiN-Schottky (MPS) diodes. With zero reverse recovery charge and 175°C maximum junction temperature, these diodes are ideally suited for high frequency and high efficiency power systems with minimum cooling requirements.



Part Number	Package	Marking
UJ3D06504TS	TO-220-2L	UJ3D06504TS

Features

- ◆ 175°C maximum operating junction temperature
- ◆ Easy paralleling
- ◆ Extremely fast switching not dependent on temperature
- ◆ No reverse or forward recovery
- ◆ Enhanced surge current capability, MPS structure
- ◆ Excellent thermal performance, Ag sintered
- ◆ 100% UIS tested
- ◆ AEC-Q101 qualified

Typical Applications

- ◆ Power converters
- ◆ Industrial motor drives
- ◆ Switching-mode power supplies
- ◆ Power factor correction modules

Maximum Ratings

Parameter	Symbol	Test Conditions	Value	Units
DC blocking voltage	V_R		650	V
Repetitive peak reverse voltage, $T_j=25^\circ\text{C}$	V_{RRM}		650	V
Surge peak reverse voltage	V_{RSM}		650	V
Maximum DC forward current	I_F	$T_C = 156^\circ\text{C}$	4	A
Non-repetitive forward surge current sine halfwave	I_{FSM}	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	29	A
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	26	
Repetitive forward surge current sine halfwave, $D=0.1$	I_{FRM}	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	23.2	A
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	13.6	
Non-repetitive peak forward current	$I_{F,max}$	$T_C = 25^\circ\text{C}, t_p = 10\mu\text{s}$	260	A
		$T_C = 110^\circ\text{C}, t_p = 10\mu\text{s}$	260	
i^2t value	$\int i^2 dt$	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	4.2	A^2s
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	3.4	
Power dissipation	P_{Tot}	$T_C = 25^\circ\text{C}$	71.4	W
		$T_C = 156^\circ\text{C}$	9	
Maximum junction temperature	$T_{J,max}$		175	$^\circ\text{C}$
Operating and storage temperature	T_J, T_{STG}		-55 to 175	$^\circ\text{C}$
Soldering temperatures, wavesoldering only allowed at leads	T_{sold}	1.6mm from case for 10s	260	$^\circ\text{C}$

Electrical Characteristics

$T_J = +25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Forward voltage	V_F	$I_F=4\text{A}, T_J=25^\circ\text{C}$	-	1.5	1.7	V
		$I_F=4\text{A}, T_J=150^\circ\text{C}$	-	1.9	2.1	
		$I_F=4\text{A}, T_J=175^\circ\text{C}$	-	2.05	2.25	
Reverse current	I_R	$V_R=650\text{V}, T_J=25^\circ\text{C}$	-	0.7	25	μA
		$V_R=650\text{V}, T_J=175^\circ\text{C}$	-	5		
Total capacitive charge ⁽¹⁾	Q_C	$V_R=400\text{V}$		9.3		nC
Total capacitance	C	$V_R=1\text{V}, f=1\text{MHz}$		118		pF
		$V_R=300\text{V}, f=1\text{MHz}$		16		
		$V_R=600\text{V}, f=1\text{MHz}$		15		
Capacitance stored energy	E_C	$V_R=400\text{V}$		1.4		μJ

(1) Q_C is independent on T_J , di_F/dt , and I_F as shown in the application note USCi_AN0011.

Thermal characteristics

Parameter	symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Thermal resistance, junction - case	$R_{\theta JC}$			1.6	2.1	$^\circ\text{C}/\text{W}$

Typical Performance

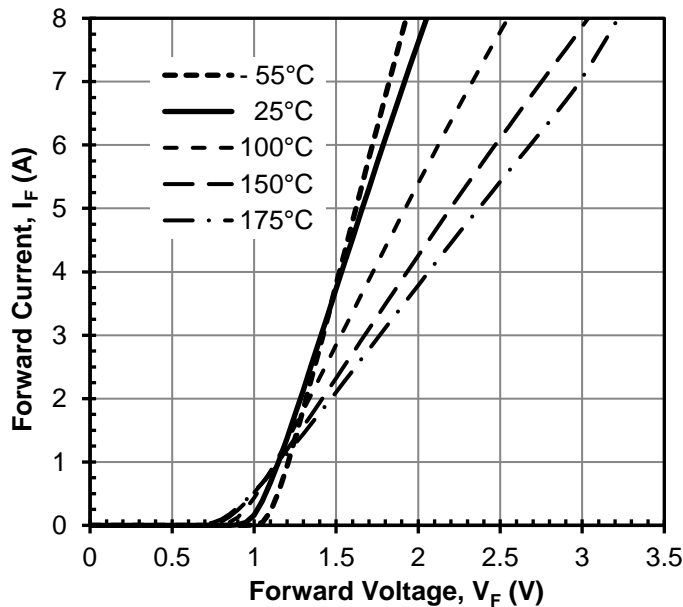


Figure 1 Typical forward characteristics

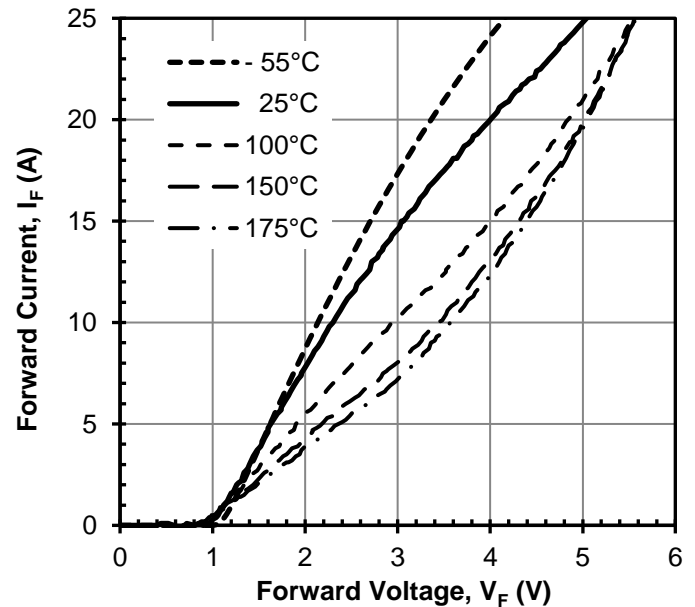
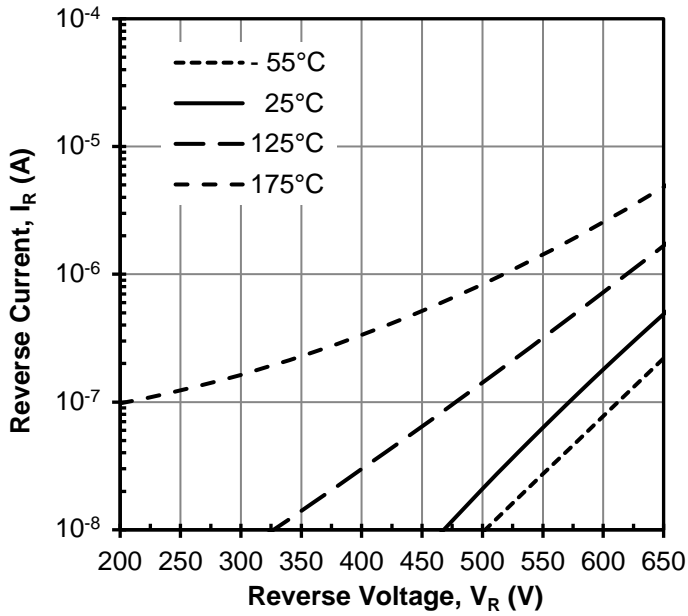
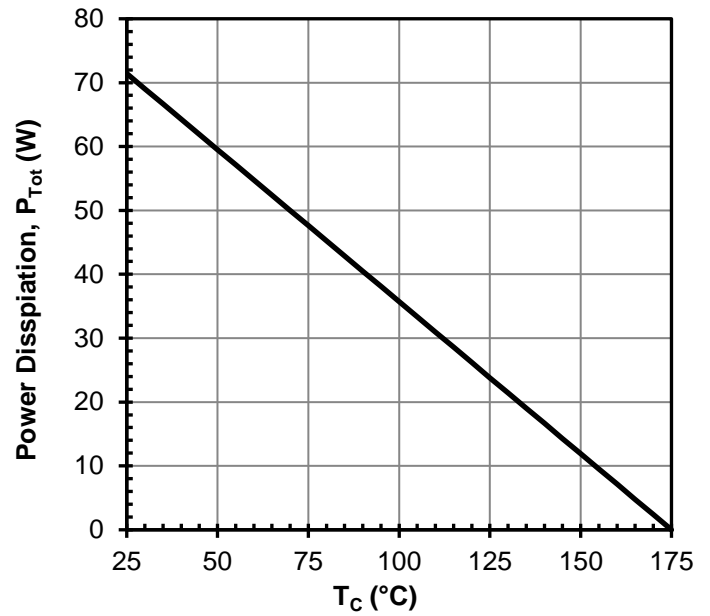
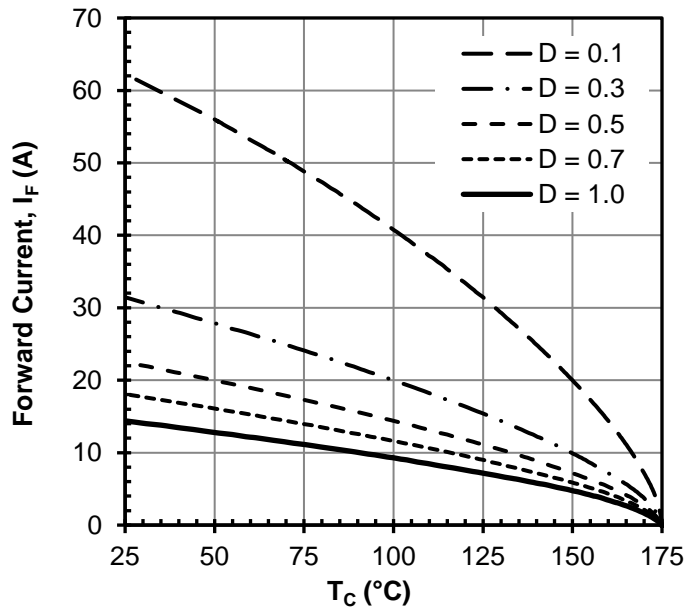
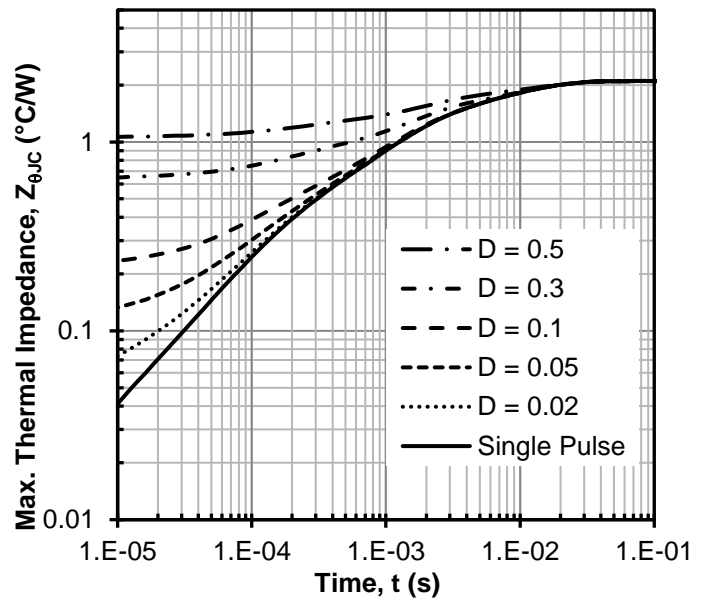


Figure 2 Typical forward characteristics in surge current


Figure 3 Typical reverse characteristics

Figure 4 Power dissipation

Figure 5 Diode forward current

Figure 6 Maximum transient thermal impedance

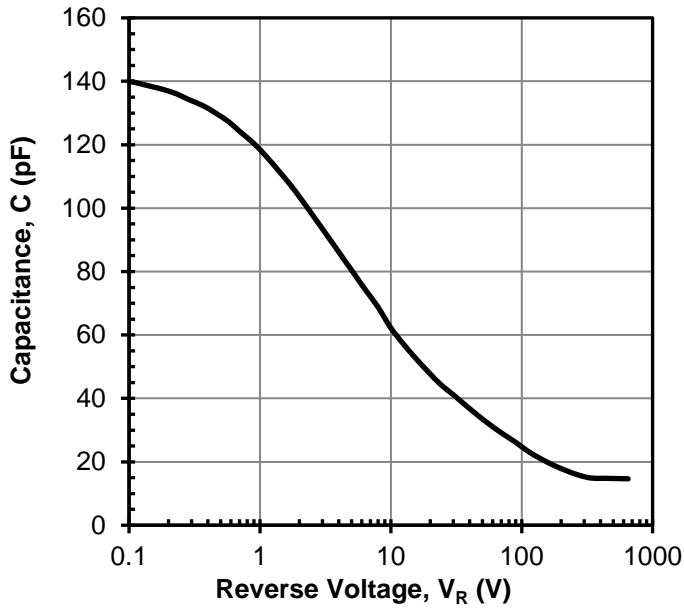


Figure 7 Capacitance vs. reverse voltage at 1MHz

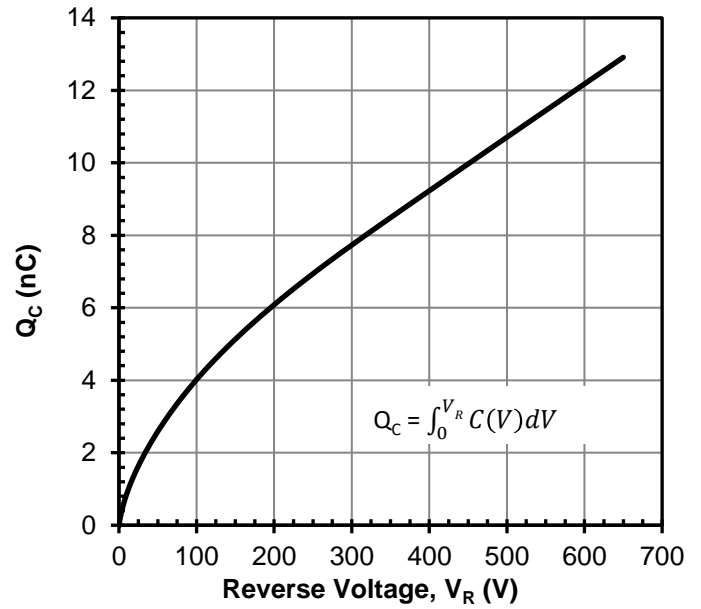


Figure 8 Typical capacitive charge vs. reverse voltage

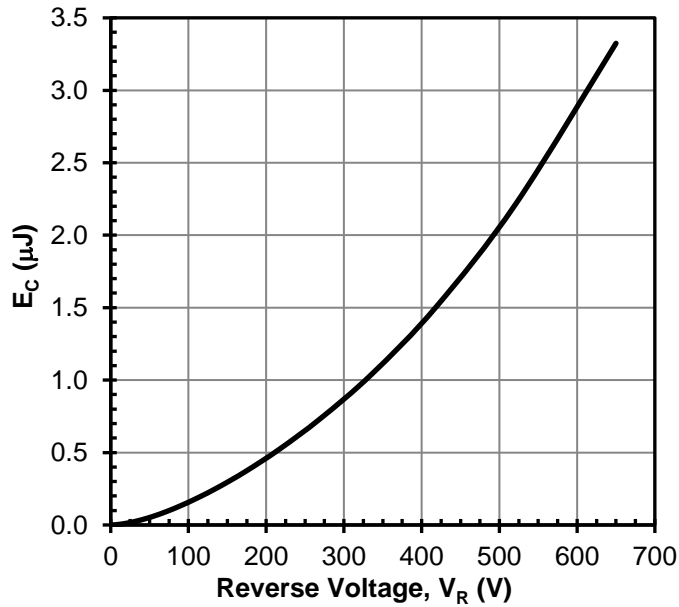


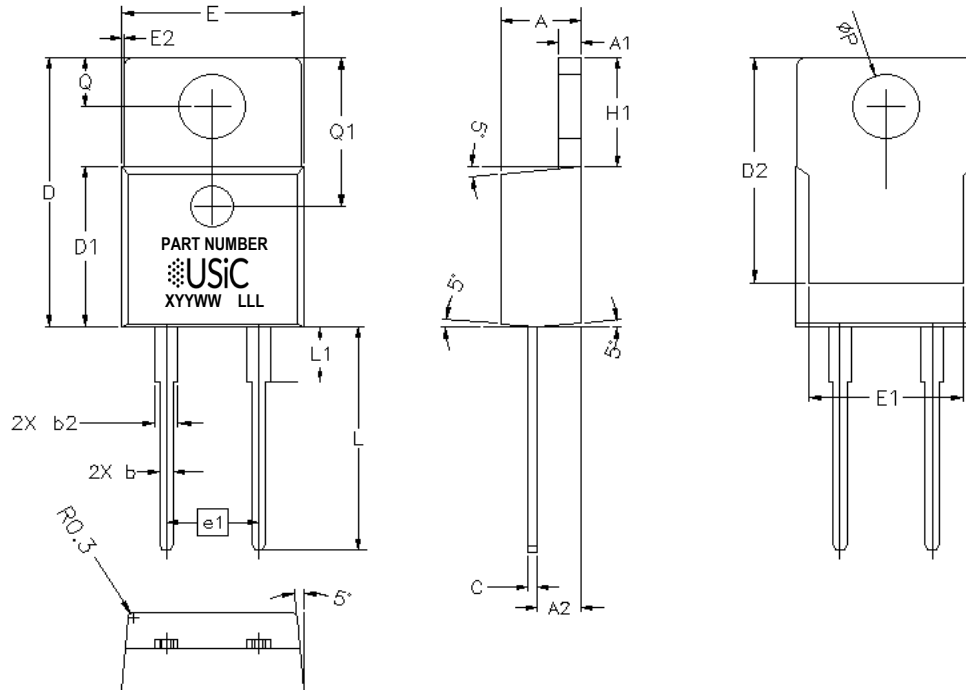
Figure 9 Typical capacitance stored energy vs. reverse voltage

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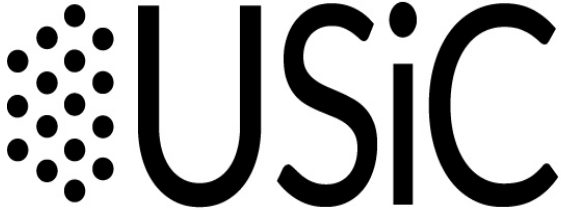
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PACKAGE OUTLINE


DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.140	0.190	3.56	4.83
A1	0.020	0.055	0.51	1.40
A2	0.080	0.115	2.03	2.92
b	0.015	0.040	0.38	1.02
b2	0.040	0.070	1.02	1.78
C	0.014	0.030	0.36	0.76
D	0.560	0.650	14.22	16.51
D1	0.330	0.370	8.38	9.40
D2	0.480	0.517	12.19	13.13
E	0.380	0.420	9.65	10.67
e1	0.200 BSC		5.08 BSC	
E1	0.270	0.350	6.86	8.89
E2	-	0.030		0.76
L	0.495	0.580	12.57	14.73
L1	-	0.250	-	6.35
ØP	0.139	0.161	3.53	4.09
H	0.230	0.270	5.84	6.86
Q	0.100	0.135	2.54	3.43
Q1	0.330	0.340	8.38	8.64

PART MARKING

PART NUMBER

XYYWW LLL

PART NUMBER = REFER TO
DS_PN DECODER FOR DETAILS

X = ASSEMBLY SITE

YY = YEAR

WW = WORK WEEK

LLL = LOT ID

PACKING TYPE

ANTI-STATIC TUBE

QUANTITY /TUBE : 50 UNITS

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